

S5D10170H2 S5D10170A2



Data Sheet N2630, REV.-S5D10170H2 S5D10170A2 1700V SIC POWER SCHOTTKY RECTIFIERS

Description

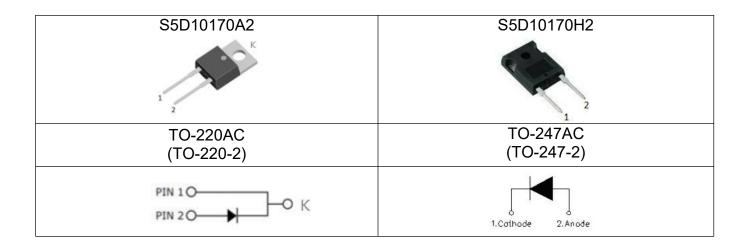
S5D10170H2/S5D10170A2 are SiC Schottky rectifiers packaged in TO-247AC(TO-247-2) and TO-220AC(TO-220-2) case. The device is high voltage Schottky rectifier that has very low total conduction losses and very stable switching characteristics over temperature extremes. The S5D10170H2/S5D10170A2 are ideal for energy sensitive, high frequency applications in challenging environments.

Features

- 175°C T_J operation
- Ultra-low switching loss
- Switching speeds independent of operating temperature
- Low total conduction losses
- High forward surge current capability
- High package isolation voltage
- Terminals finish: 100% Pure Tin
- Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional electrical and life testing can be performed upon request

Applications

- Alternative energy inverters
- Power Factor Correction (PFC)
- Free-Wheeling diodes
- Switching supply output rectification
- Reverse polarity protection





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Maximum Ratings



RoHS 🗭

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	-	1700	V
Average Destified Ferward Current	I _{F (AV)1}	Tc=25°C	44	A
Average Rectified Forward Current	IF (AV)2	Tc=161°C	10	А
Peak One Cycle Non-Repetitive Surge	I _{FSM1}	/RRM VR - (AV)1 Tc=25°C (AV)2 Tc=161°C FSM1 10ms, Half Sine pulse, Tc=25°C FSM2 10ms, Half Sine pulse, Tc=110°C FRM1 10 ms, Half Sine pulse, Tc=25°C FRM2 10 ms, Half Sine pulse, Tc=25°C IQMS, Half Sine pulse, Tc=25°C 10 ms, Half Sine pulse, Tc=110°C FRM2 10 µs. Pulse, Tc=25°C FMax1 10µs. Pulse, Tc=110°C Ptot1 Tc=25°C	230	А
Current	I _{FSM2}		210	А
Denetitive Deels Ferrurad Curren Current	I _{FRM1}			А
Repetitive Peak Forward Surge Current	I _{FRM2}	- Tc=25°C Tc=161°C 10ms, Half Sine pulse, Tc=25°C 10ms, Half Sine pulse, Tc=110°C 10 ms, Half Sine pulse, Tc=25°C 10 ms, Half Sine pulse, Tc=110°C 10µs. Pulse, Tc=25°C 10µs. Pulse, Tc=110°C Tc=25°C	126	А
Non-Repetitive Peak Forward Surge	I _{F,Max1}	FRM2 10 ms, Half Sine pulse , Tc =110°C 126 Max1 10µs. Pulse, Tc =25°C 400	400	A
Current	I _{F,Max2}		320	A
Power Dissinction	P _{tot1}	Tc=25℃	333.4	W
Power Dissipation	P _{tot2}	Tc=110℃	144.4	W

Electrical Characteristics:					
Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	V _{F1}	@ 10A, Pulse, T _J = 25 °C	1.5	1.8	V
	V _{F2}	@ 10A, Pulse, $T_J = 175 \degree C$ @V _R = rated V _R , $T_J = 25 \degree C$ @V _R = rated V _R , $T_J = 175 \degree C$ VR=0V, f=1MHz, Tj=25°C,	2.4	2.6	V
Reverse Current*	I _{R1}	@V _R = rated V _R , T _J = 25 °C	2	20	uA
	I _{R2}	@V _R = rated V _R , T _J = 175 °C 20		200	uA
Junction Capacitance	C _{T1}	VR=0V, f=1MHz, Tj=25℃,	978	-	pF
	C _{T2}	VR=1700V, f=1MHz, Tj=25°C, 5		-	pF
Reverse Recovery Charge	Qc	I _F = 10A, di/dt = 200A/µs VR = 1700 V, T _J =25°C		-	nC
Capacitance Stored Energy	Ec	V _R = 1700 V, T _J =25°C	131.33	-	μJ

* Pulse width < 300 μ s, duty cycle < 2%



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RoHS 🗭

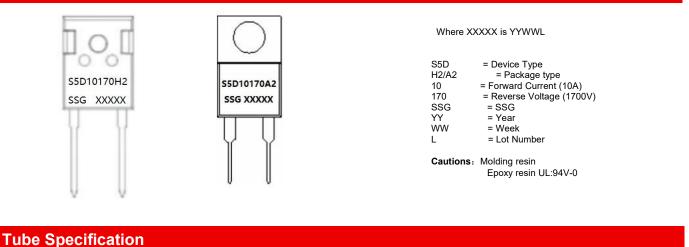
Thermal-Mechanical Specifications:

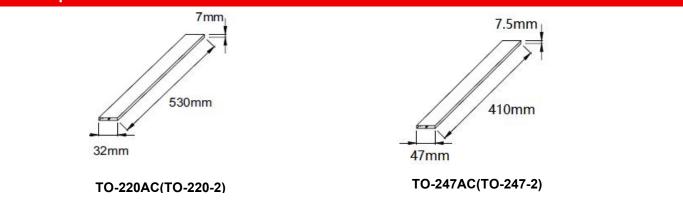
Characteristics	Symbol	S5D10170H2	S5D10170A2	Units
Junction Temperature	TJ	55 to	°C	
Storage Temperature	T _{stg}	55 to	°C	
Typical Thermal Resistance Junction to Case	$R_{ ext{ ext{ extbf{ extb$	0.8	0.9	°C/W

Ordering Information

Device	Package	Shipping
S5D10170H2	TO-247AC(TO-247-2)	25pcs / tube
S5D10170A2	TO-220AC(TO-220-2)	50pcs / tube

Marking Diagram





- China Germany Korea Singapore United States •
- http://www.smc-diodes.com sales@ smc-diodes.com •







Ratings and Characteristics Curves

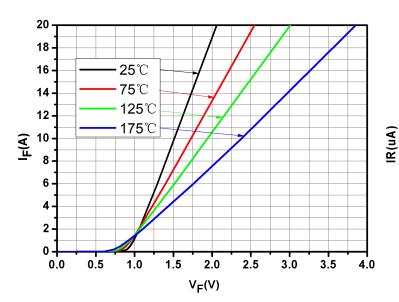


Fig.1-Typical Forward Voltage Characteristics

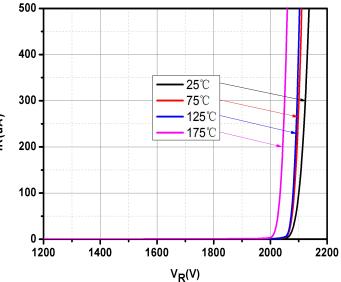


Fig.2-Typical Reverse Characteristics

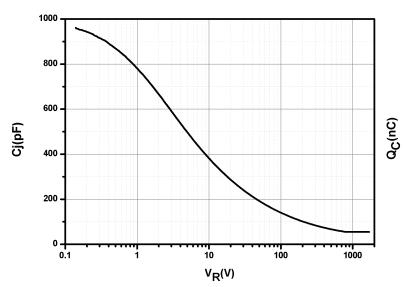


Fig.3-Capacitance vs. Reverse Voltage

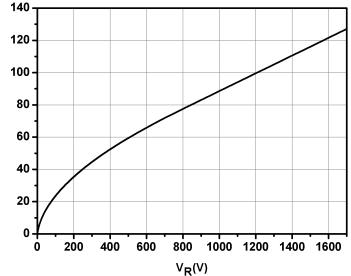


Fig.4-Total Capacitance Charge vs. Reverse Voltage



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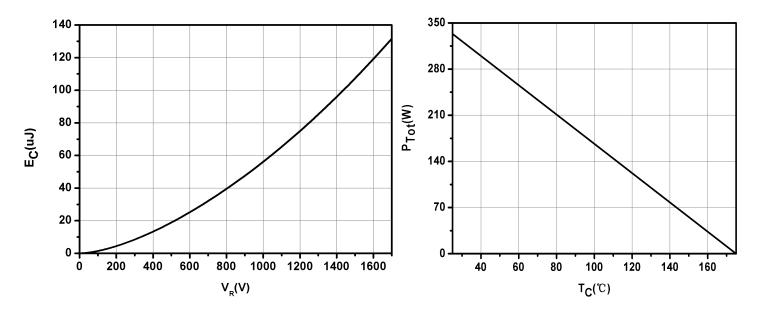


Fig.5-Capacitance Stored Energy

Fig.7-Power Derating

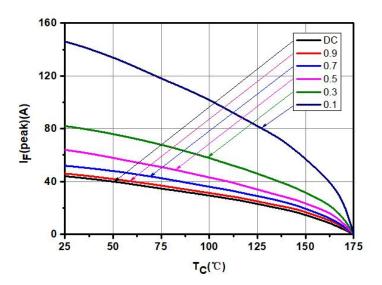


Fig.8-Current Derating

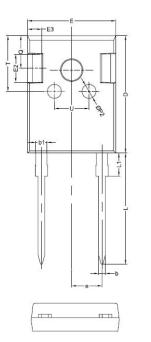


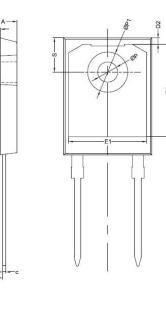
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Mechanical Dimensions TO-247AC(TO-247-2)

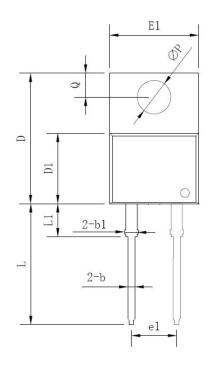


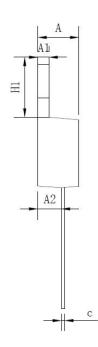


SYMBOL	Millimeters			
	MIN.	TYP.	MAX.	
Α	4.80	5.00	5.20	
A1	2.20	2.41	2.61	
A2	1.90	2.00	2.10	
b	1.10	1.20	1.35	
b1	1.80	2.00	2.20	
С	0.50	0.60	0.75	
D	20.30	21.00	21.20	
D1		16.58		
D2		1.17		
E	15.60	15.80	16.00	
E1		14.02		
E2		5.00		
E3		2.50		
е		5.44		
L	19.42	19.92	20.42	
L1		4.13		
Р	3.50	3.60	3.70	
P1	7.1	7.19	7.40	
P2		2.50		
Q		5.80		
S	6.05	6.15	6.25	
Т		10.00		
U		6.20		

Mechanical Dimensions TO-220AC(TO-220-2)

Δ1





Symbol	Dimensions in millimeters			
	Min.	Typical	Max.	
A	3.56	-	4.83	
A1	0.51	-	1.40	
A2	2.03	-	2.92	
b	0.38	-	1.02	
b1	1.14	-	1.78	
с	0.31	-	0.61	
D	14.22	-	16.51	
D1	8.38	-	9.42	
E1	9.65	10.16	10.67	
e1	-	5.08	-	
H1	5.84	-	6.86	
L	12.70	-	14.73	
L1	-	-	6.35	
ΦΡ	-	3.56	-	
Q	2.54	-	3.43	



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